

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE

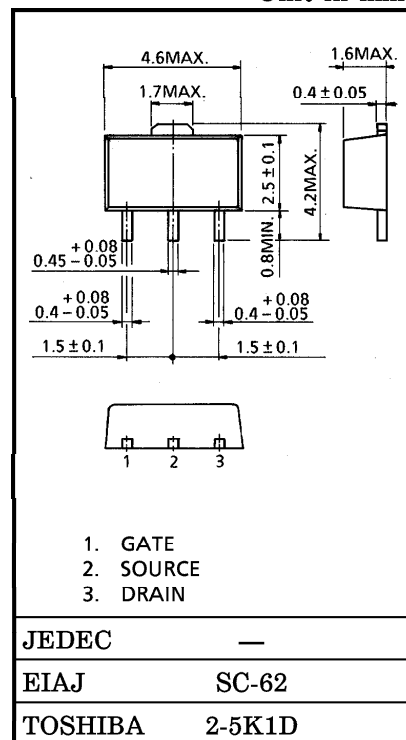
# 2SK2855

UHF BAND AMPLIFIER APPLICATION

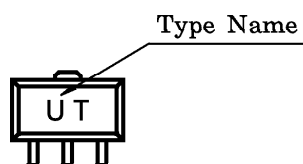
Unit in mm

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V <sub>DSS</sub>	10	V
Gate-Source Voltage	V <sub>GS</sub>	±6	V
Drain Current	I <sub>D</sub>	1.0	A
Drain Power Dissipation	P <sub>D</sub>	0.5	W
Channel Temperature	T <sub>ch</sub>	150	°C
Storage Temperature Range	T <sub>stg</sub>	-55~150	°C



MARKING



ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Output Power	P <sub>O</sub>	V <sub>DS</sub> = 6V, f = 849MHz P <sub>i</sub> = 23dBmW	31	—	—	dBmW
Drain Efficiency	η <sub>D</sub>	V <sub>DS</sub> = 6V, f = 849MHz P <sub>i</sub> = 23dBmW, P <sub>O</sub> = 31dBmW	55	—	—	%
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0, I <sub>D</sub> = 1μA	10	—	—	V
Drain Cut-off Current	I <sub>DSS</sub>	V <sub>DS</sub> = 6V, V <sub>GS</sub> = 0	—	—	100	nA
Threshold Voltage	V <sub>th</sub>	V <sub>DS</sub> = 6V, I <sub>D</sub> = 500μA	1.0	1.4	1.8	V
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = 6V, V <sub>DS</sub> = 0	—	—	±100	nA

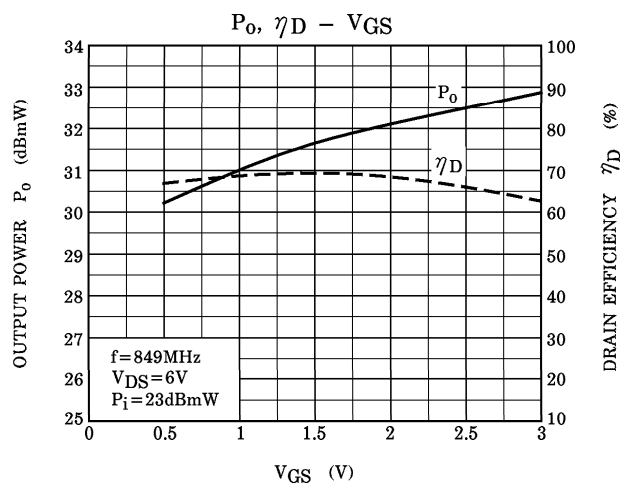
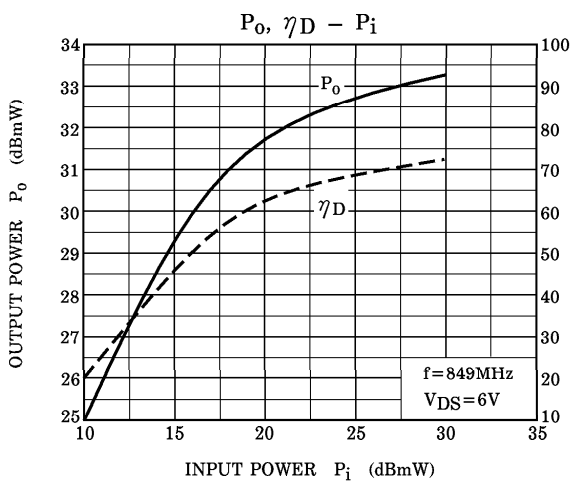
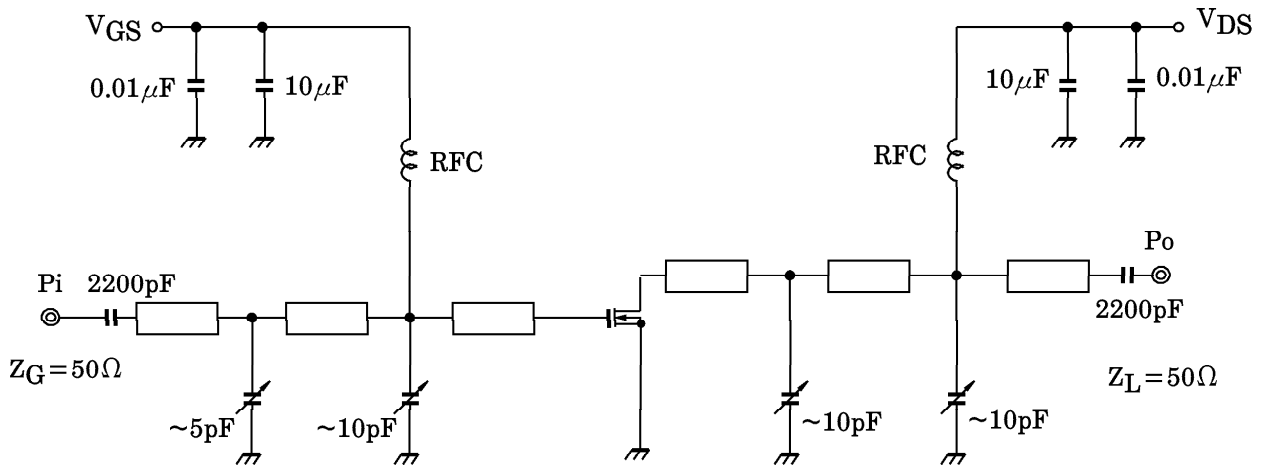
CAUTION

This transistor is the electrostatic sensitive device.  
Please handle with caution.

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RF OUTPUT POWER TEST FIXTURE



CAUTION

These are only typical curves and devices are not necessarily guaranteed at these curves.